





Fig. 5

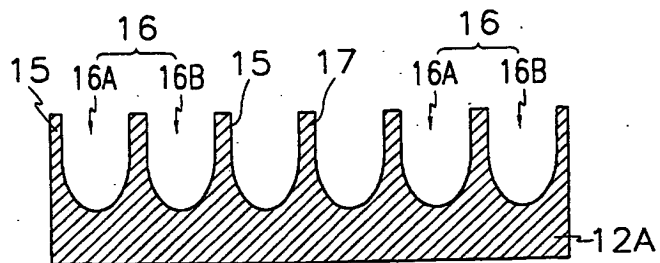


Fig. 6

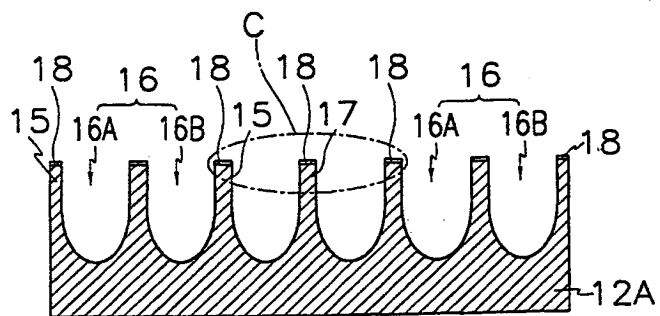
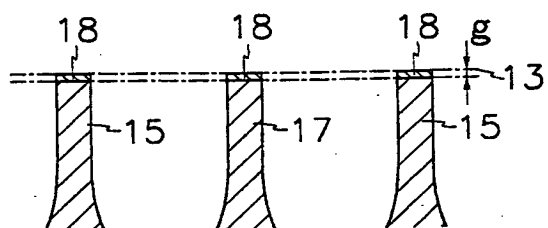
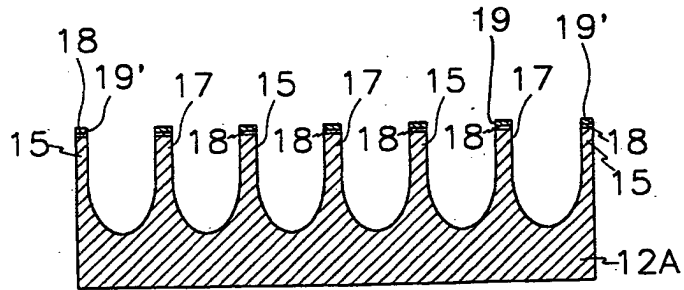


Fig. 7



This diagram shows a cross-sectional view of a substrate assembly. A base layer, labeled 12A, is shown with diagonal hatching. On top of this base, there is a series of alternating layers. A layer labeled 15 is positioned above the base, with a series of notches or recesses cut into it. The notches are filled with a material labeled 18. The top surface of the notches is labeled 19, and the side walls of the notches are labeled 19'. The layer 15 is also labeled with 17 in the recessed areas. The overall structure is shown in a perspective view, with the notches repeating across the width of the substrate.



20 20 20 20 20 20  
(R) (R) (G) (G) (B) (B)

12

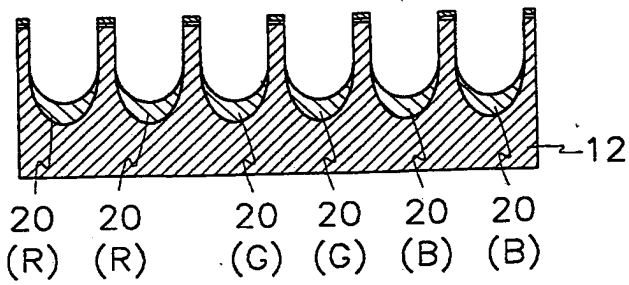


FIG. 1 is a cross-sectional view of a first embodiment of a semiconductor device. The device consists of a substrate 10. The top surface of the substrate is labeled 12A. Along the top surface 12A, there is a series of small, rectangular features or structures, each labeled 18. These features are spaced apart from each other.

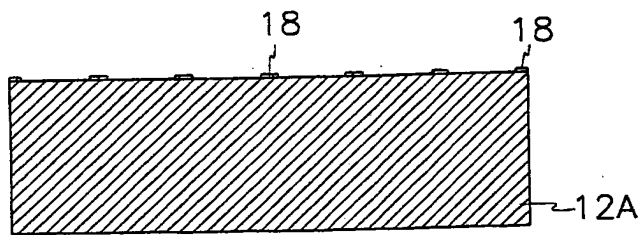


Fig. 11

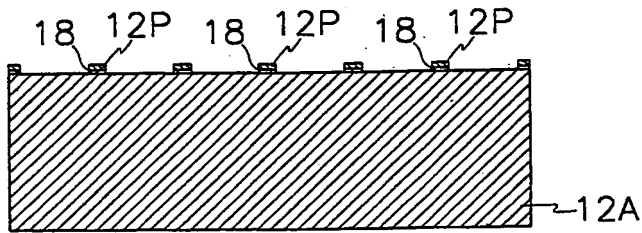


Fig. 12

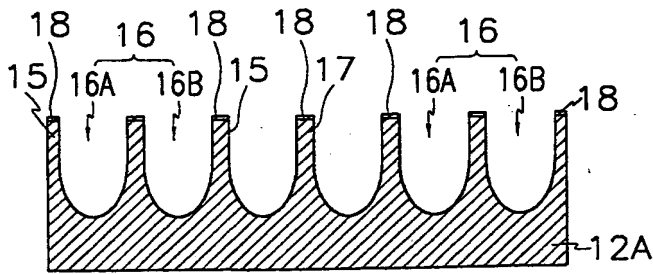


Fig. 13

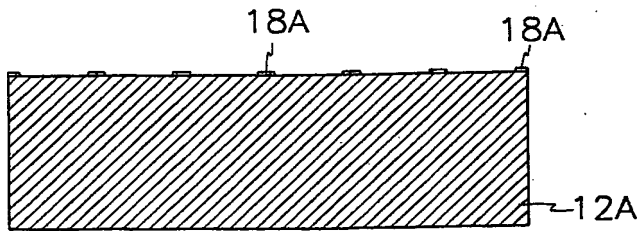
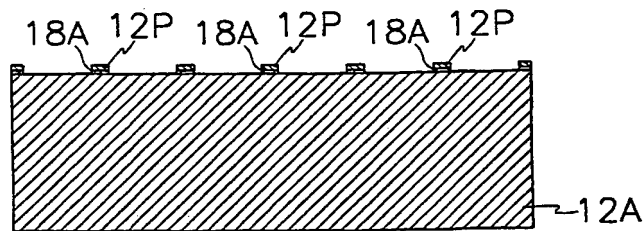


Fig. 14



205110-1502

Fig. 15

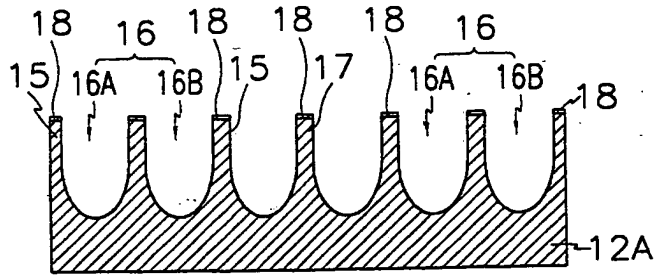


Fig. 16

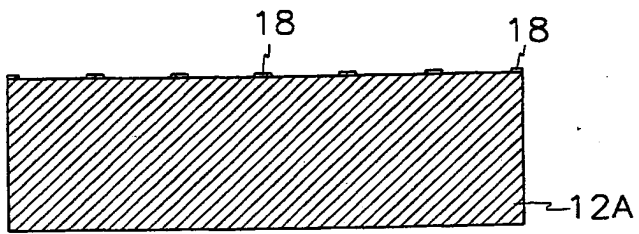


Fig. 17

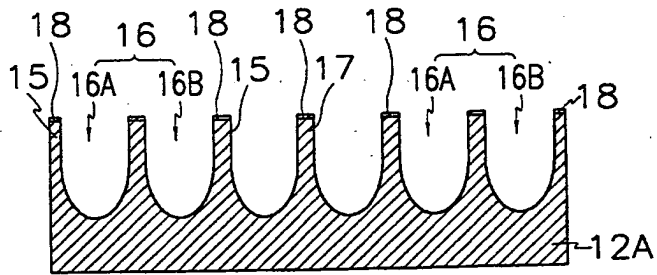


Fig. 18

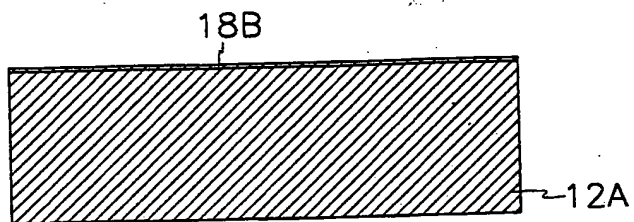


Fig. 19

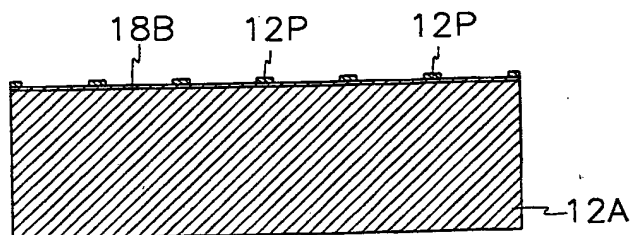


Fig. 20

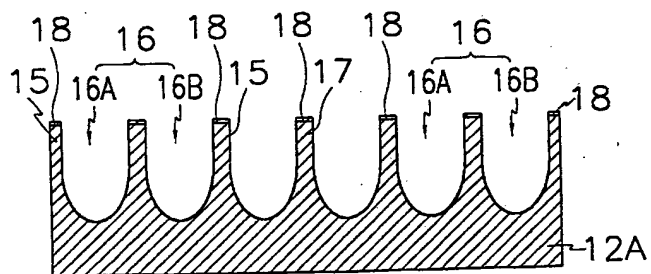


Fig. 21

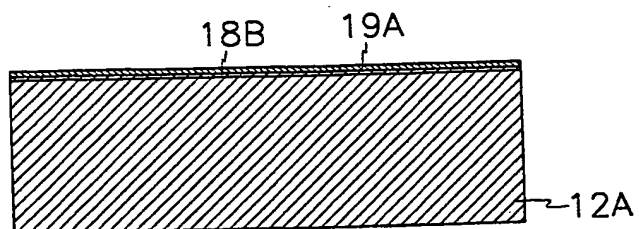


Fig. 22

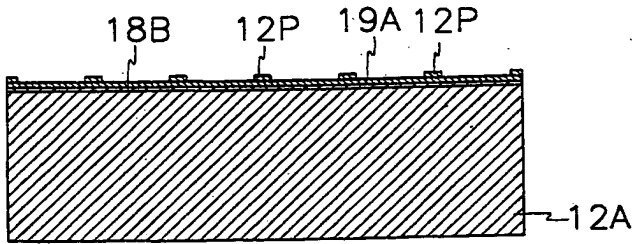


Fig. 23

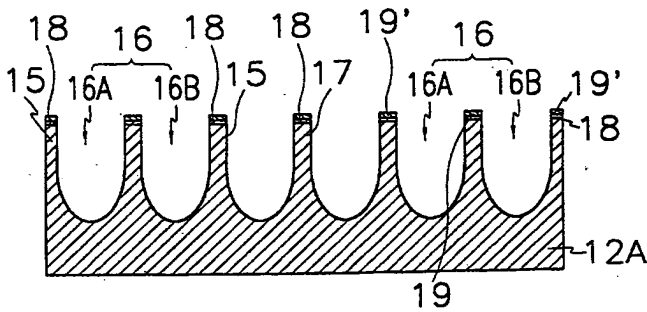
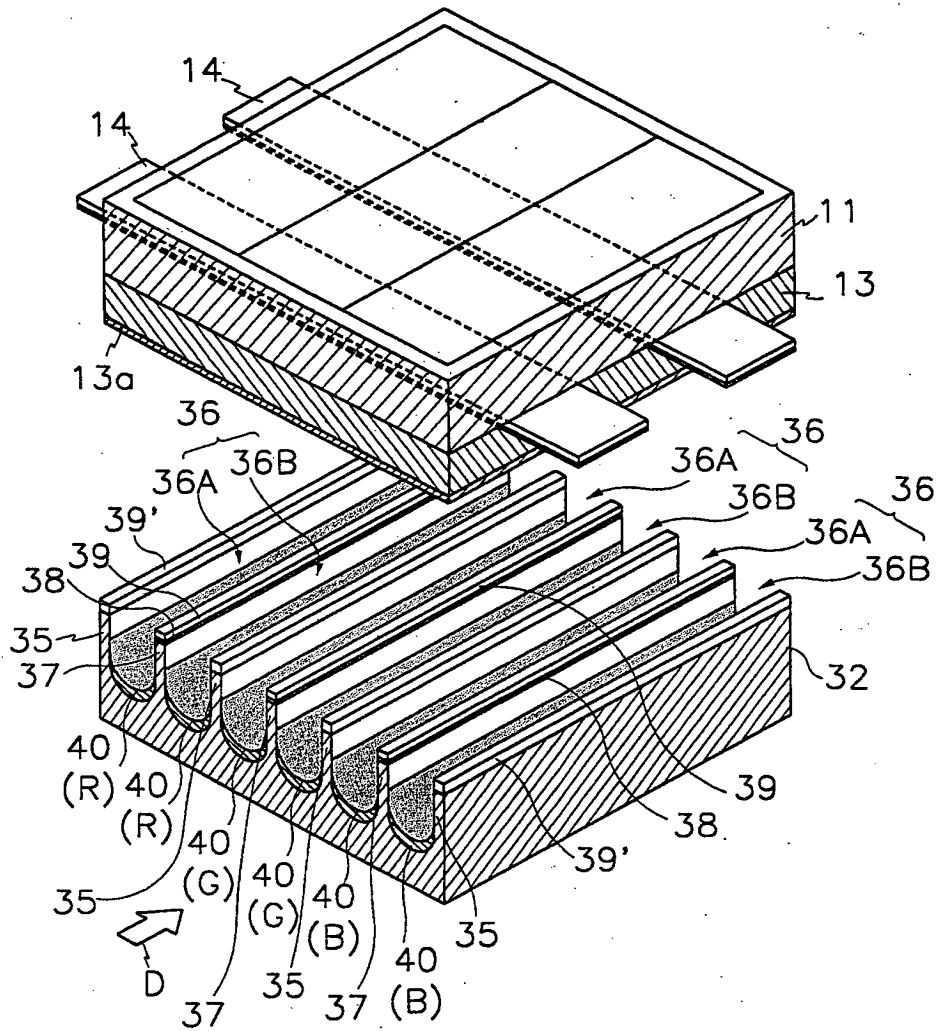




Fig. 24



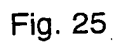


Fig. 27

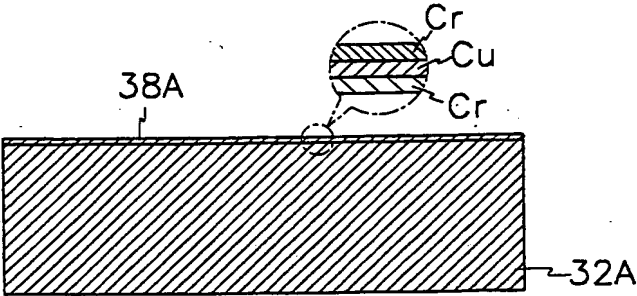


Fig. 28

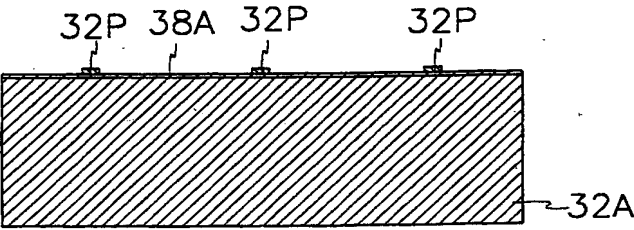


Fig. 29

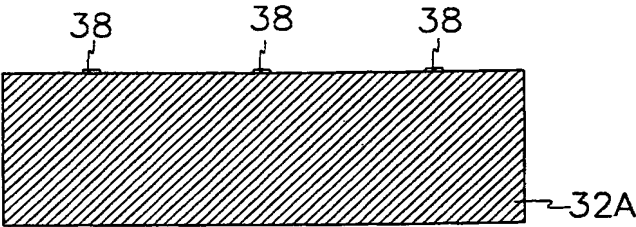


Fig. 30

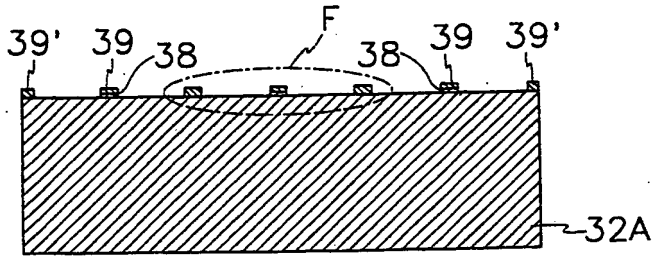


Fig. 31

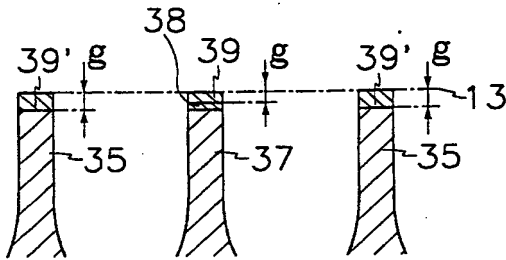
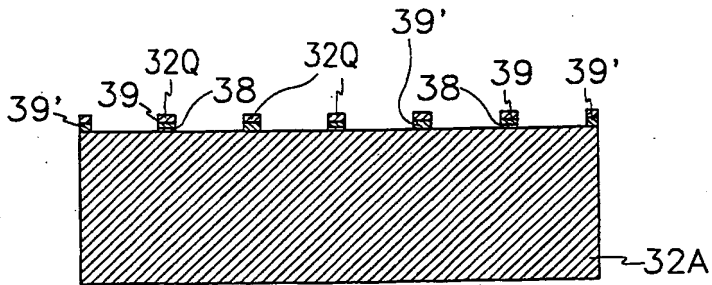


Fig. 32



205110" / T05400T  
10045017.011502

Fig. 33

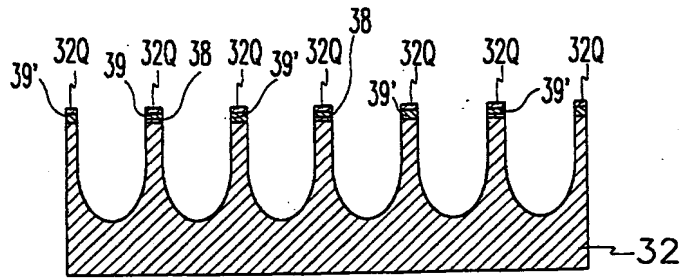


Fig. 34

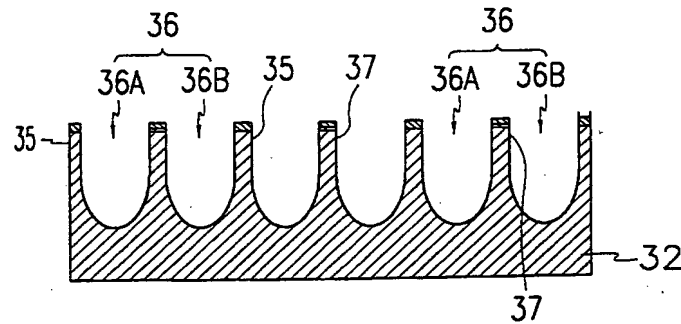


Fig. 35

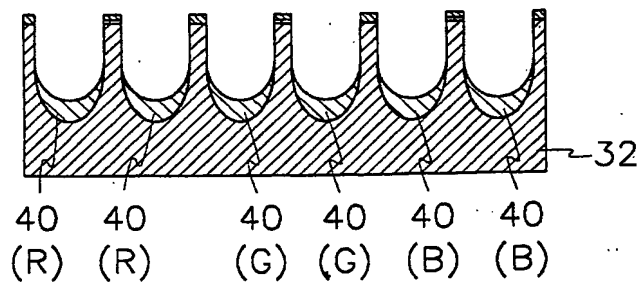




Fig. 37

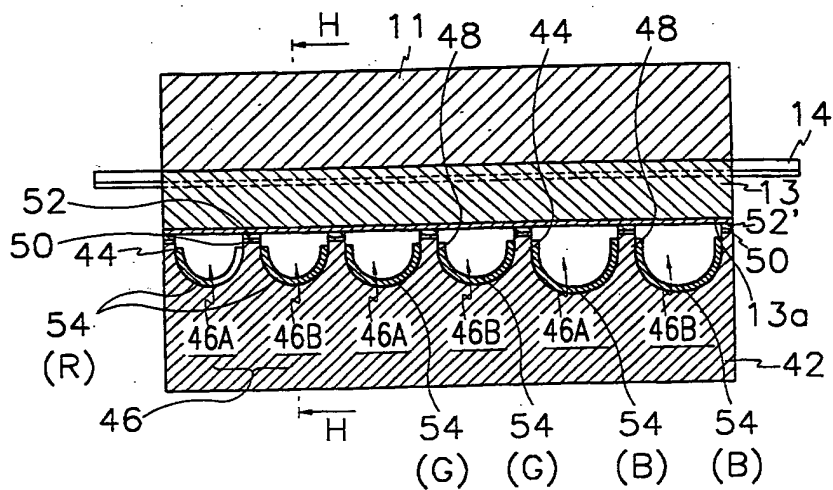


Fig. 38

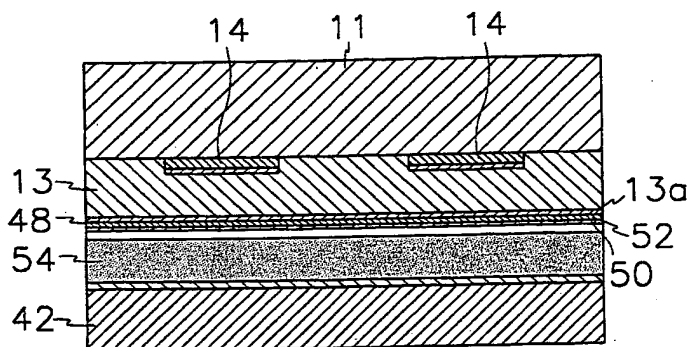


Fig. 39

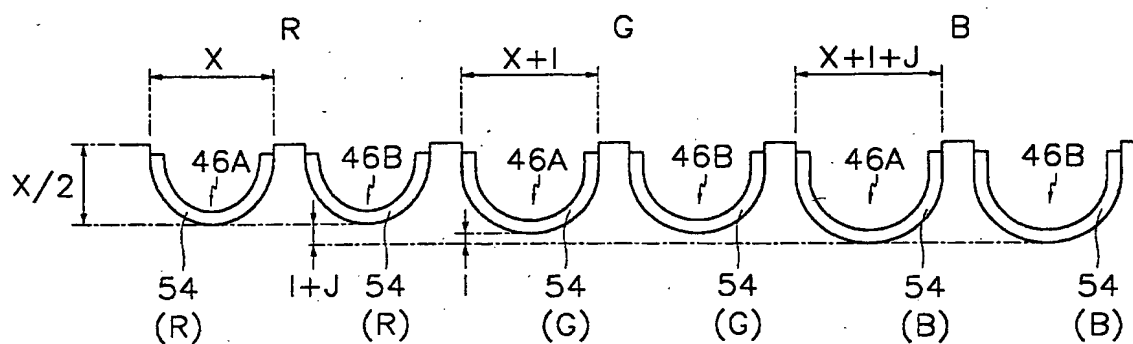
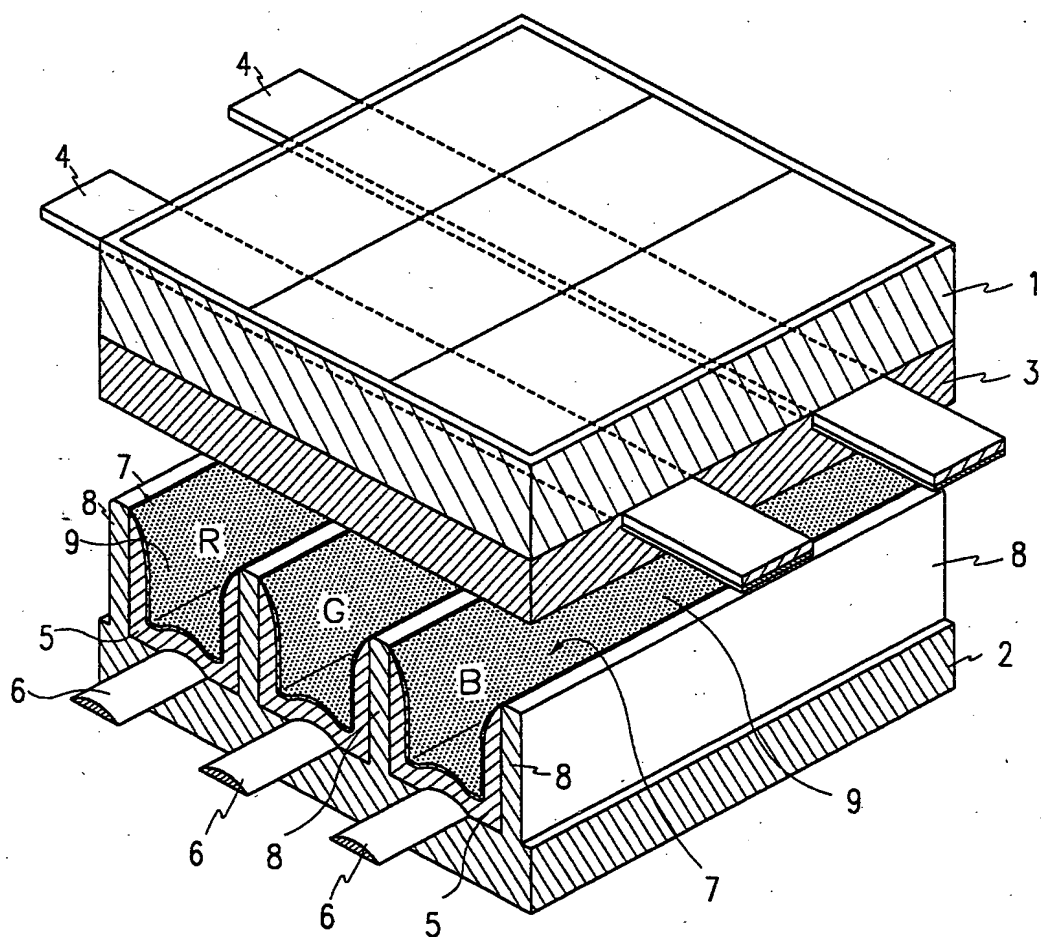


Fig. 40 (Prior Art)



205710-27054001